



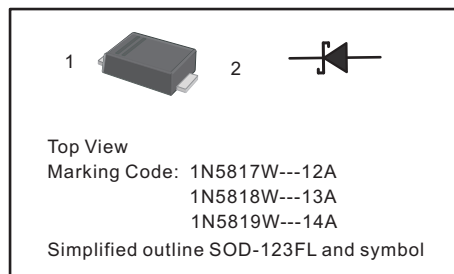
## SCHOTTKY BARRIER RECTIFIERS

### FEATURES

- Metal silicon junction, majority carrier conduction
- Guarding for overvoltage protection
- Low power loss, high efficiency
- High current capability
- low forward voltage drop
- High surge capability
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications

### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



### MECHANICAL DATA

- Case: SOD-123FL
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 15mg 0.00048oz

### Maximum Ratings and Electrical characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter	Symbols	1N5817W	1N5818W	1N5819W	Units
Maximum Repetitive Peak Reverse Voltage	$V_{RRM}$	20	30	40	V
Maximum RMS voltage	$V_{RMS}$	14	21	28	V
Maximum DC Blocking Voltage	$V_{DC}$	20	30	40	V
Maximum Average Forward Rectified Current	$I_{F(AV)}$	1			A
Peak Forward Surge Current, 8.3ms Single Half Sine-wave Superimposed On Rated Load (JEDEC method)	$I_{FSM}$	25			A
Maximum Instantaneous Forward Voltage at 1 A at 3 A	$V_F$	0.45 0.75	0.55 0.875	0.6 0.9	V
Maximum Instantaneous Reverse Current at $T_A = 25^\circ\text{C}$ Rated DC Reverse Voltage $T_A = 100^\circ\text{C}$	$I_R$	1 10			mA
Typical Junction Capacitance	$C_j$	110			pF
Storage and Operating Junction Temperature Range	$T_j, T_{stg}$	-55 ~ +125			°C



Fig.1 Forward Current Derating Curve

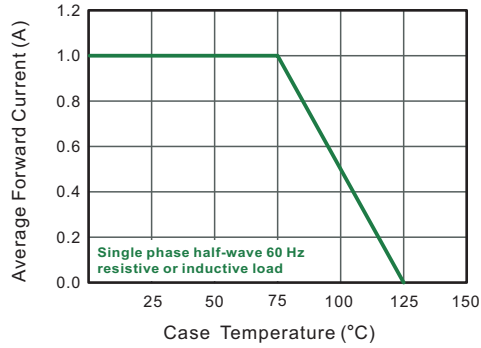


Fig.2 Typical Reverse Characteristics

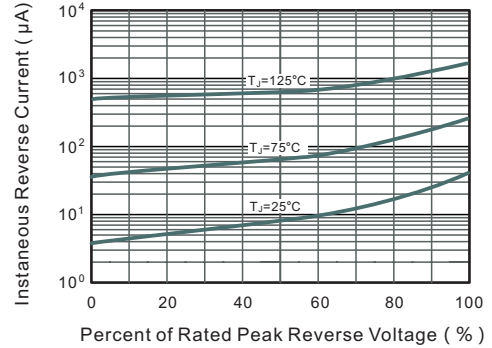


Fig.3 Typical Forward Characteristic

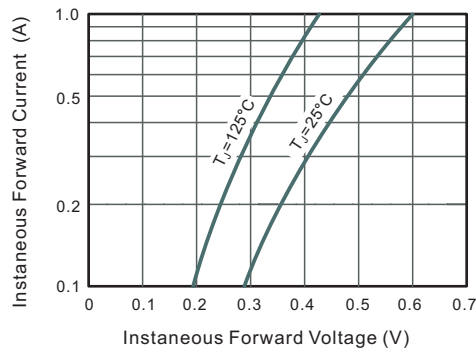


Fig.4 Typical Junction Capacitance

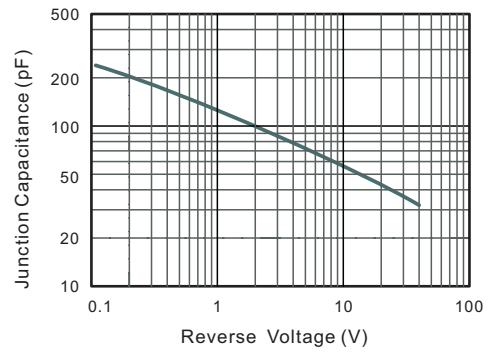
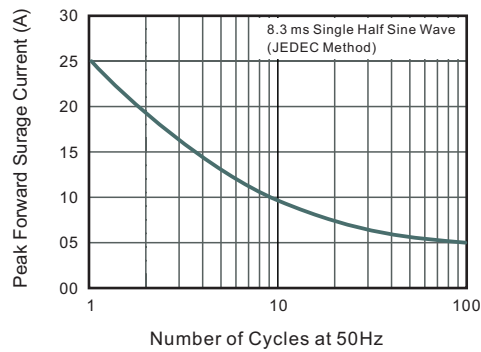


Fig.5 Maximum Non-Repetitive Peak Forward Surge Current

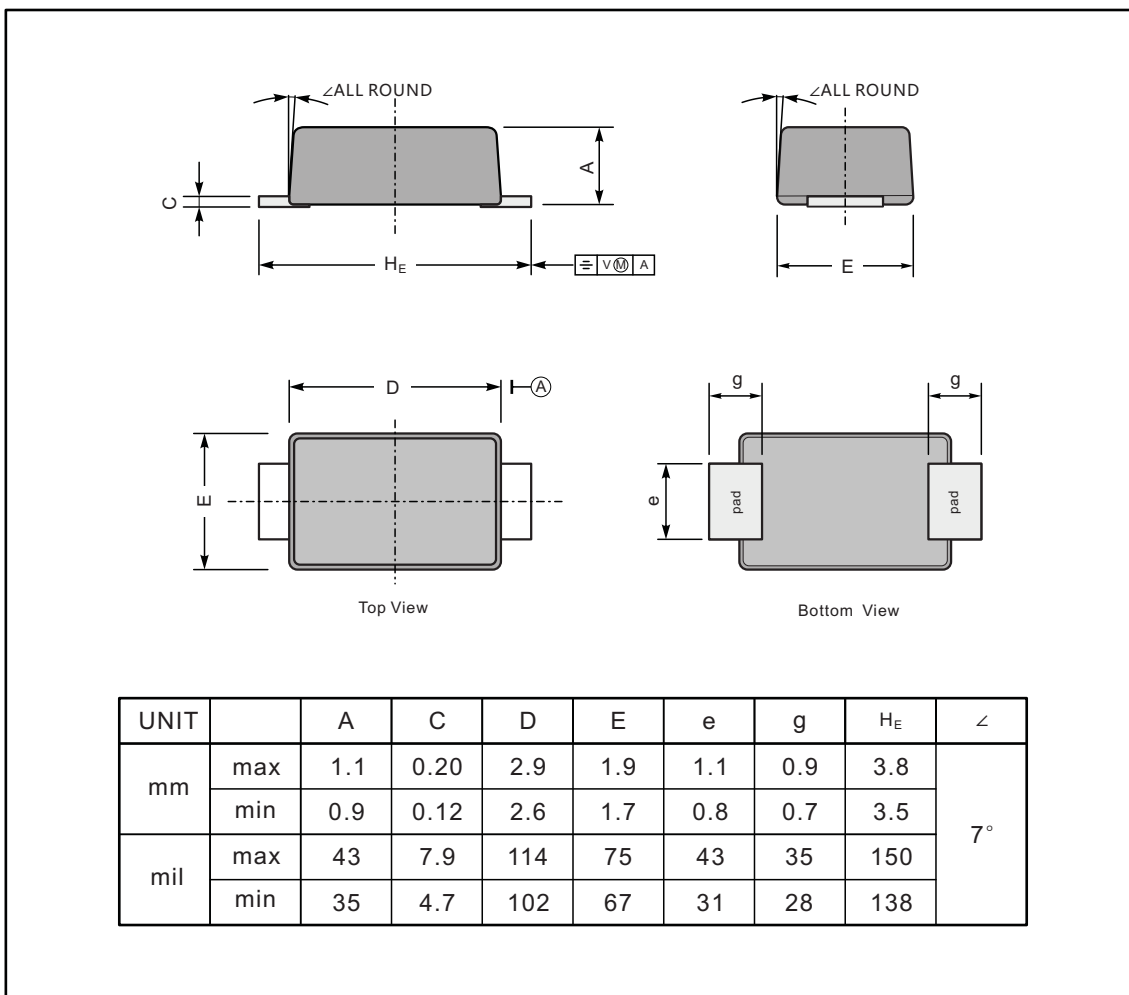




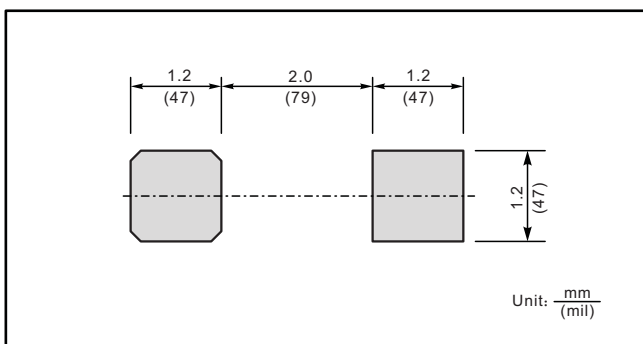
**PACKAGE OUTLINE**

Plastic surface mounted package; 2 leads

SOD-123FL



**The recommended mounting pad size**



**Marking**

Type number	Marking code
1N5817W	12A
1N5818W	13A
1N5819W	14A

单击下面可查看定价，库存，交付和生命周期等信息

[>>JINGDAO\(晶导\)](#)